

TPIC6A595 POWER LOGIC 8-BIT SHIFT REGISTER

SLIS005B – APRIL 1993 – REVISED MAY 2005

- Low $r_{DS(on)}$. . . 1 Ω Typ
- Output Short-Circuit Protection
- Avalanche Energy . . . 75 mJ
- Eight 350-mA DMOS Outputs
- 50-V Switching Capability
- Devices Are Cascadable
- Low Power Consumption

description

The TPIC6A595 is a monolithic, high-voltage, high-current power logic 8-bit shift register designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other medium-current or high-voltage loads. Each open-drain DMOS transistor features an independent chopping current-limiting circuit to prevent damage in the case of a short circuit.

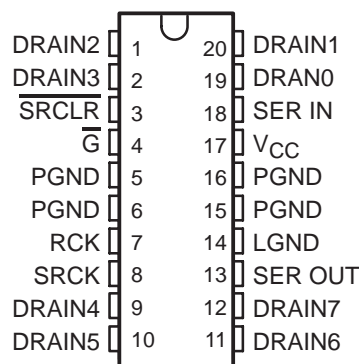
This device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit, D-type storage register. Data transfers through both the shift and storage registers on the rising edge of the shift-register clock (SRCK) and the register clock (RCK), respectively. The storage register transfers data to the output buffer when shift-register clear (SRCLR) is high. When $\overline{\text{SRCLR}}$ is low, the input shift register is cleared. When output enable ($\overline{\text{G}}$) is held high, all data in the output buffers is held low and all drain outputs are off. When $\overline{\text{G}}$ is held low, data from the storage register is transparent to the output buffers. The serial output (SER OUT) allows for cascading of the data from the shift register to additional devices.

Outputs are low-side, open-drain DMOS transistors with output ratings of 50 V and a 350-mA continuous sink current capability. When data in the output buffers is low, the DMOS-transistor outputs are off. When data is high, the DMOS-transistor outputs have sink current capability.

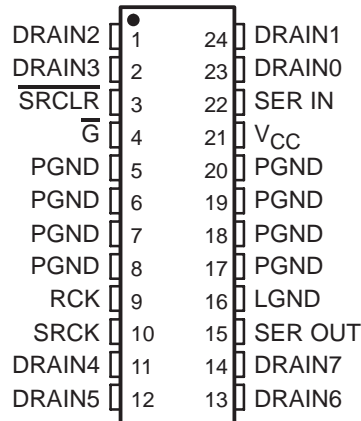
Separate power ground (PGND) and logic ground (LGND) terminals are provided to facilitate maximum system flexibility. All PGND terminals are internally connected, and each PGND terminal must be externally connected to the power system ground in order to minimize parasitic impedance. A single-point connection between LGND and PGND must be made externally in a manner that reduces crosstalk between the logic and load circuits.

The TPIC6A595 is offered in a thermally-enhanced dual-in-line (NE) package and a wide-body surface-mount (DW) package. The TPIC6A595 is characterized for operation over the operating case temperature range of -40°C to 125°C .

NE PACKAGE
(TOP VIEW)



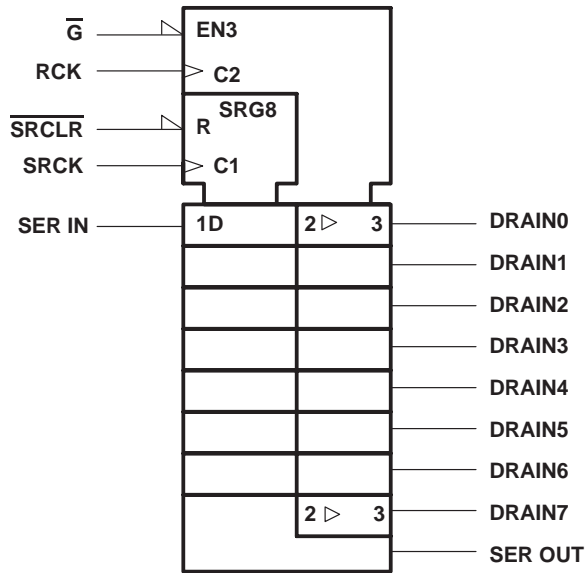
DW PACKAGE
(TOP VIEW)



TPIC6A595 POWER LOGIC 8-BIT SHIFT REGISTER

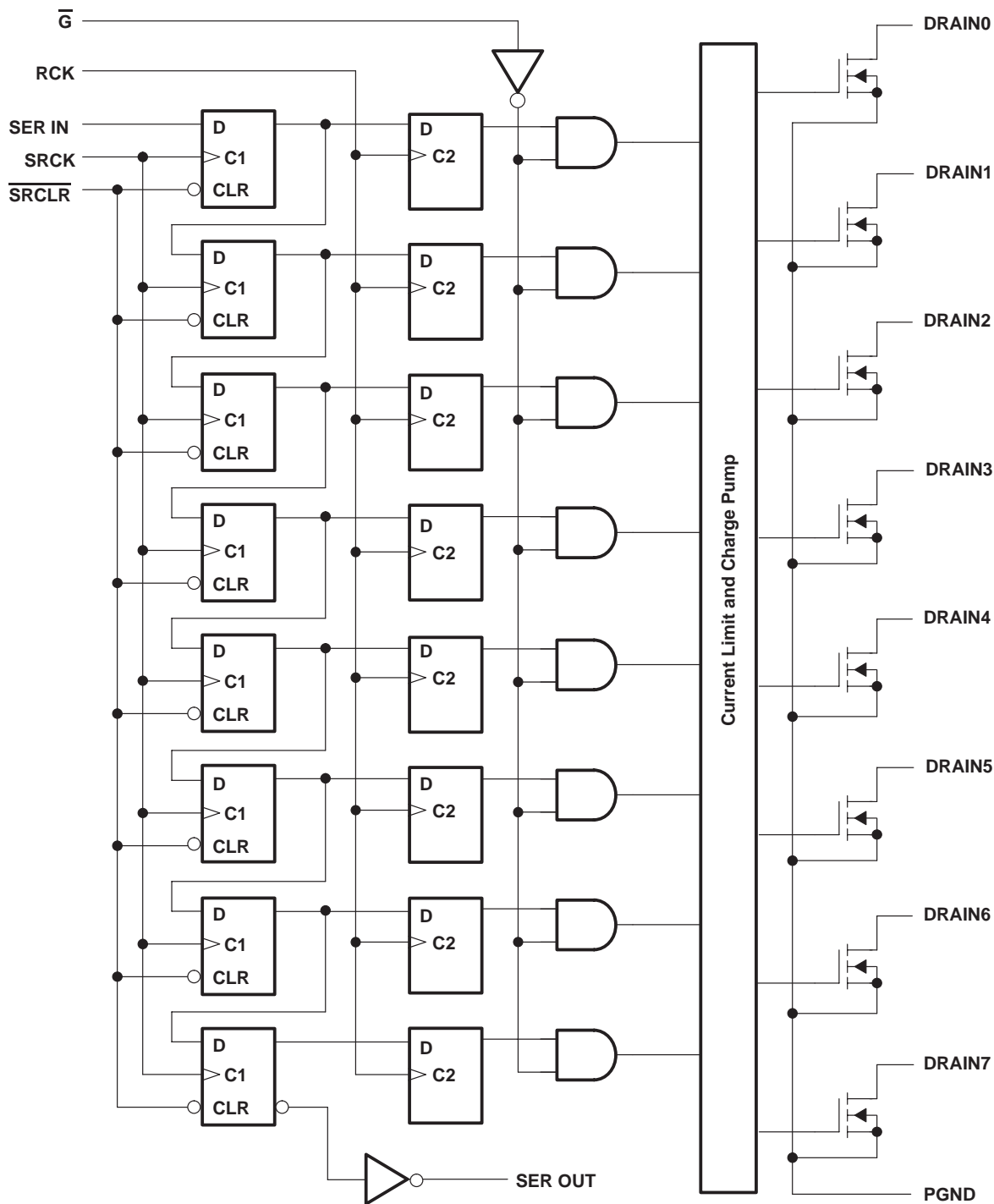
SLIS005B – APRIL 1993 – REVISED MAY 2005

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

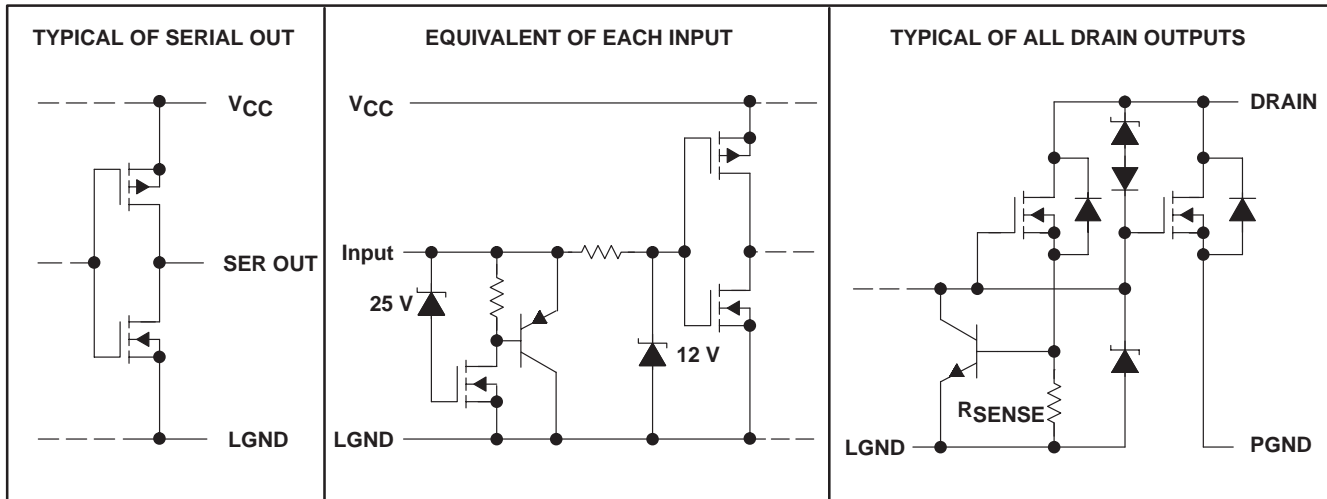
logic diagram (positive logic)



TPIC6A595 POWER LOGIC 8-BIT SHIFT REGISTER

SLIS005B – APRIL 1993 – REVISED MAY 2005

schematic of inputs and outputs



absolute maximum ratings over recommended operating case temperature range (unless otherwise noted)†

Logic supply voltage, V_{CC} (see Note 1)	7 V
Logic input voltage range, V_I	-0.3 V to 7 V
Power DMOS drain-to-source voltage, V_{DS} (see Note 2)	50 V
Continuous source-drain diode anode current	1 A
Pulsed source-drain diode anode current (see Note 3)	2 A
Pulsed drain current, each output, all outputs on, I_{Dn} , $T_A = 25^\circ\text{C}$ (see Note 3)	1.1 A
Continuous drain current, each output, all outputs on, I_{Dn} , $T_A = 25^\circ\text{C}$	350 mA
Peak drain current, single output, $T_A = 25^\circ\text{C}$ (see Note 3)	1.1 A
Single-pulse avalanche energy, E_{AS} (see Figure 6)	75 mJ
Avalanche current, I_{AS} (see Note 4)	600 mA
Continuous total dissipation	See Dissipation Rating Table
Operating case temperature range, T_C	-40°C to 125°C
Operating virtual junction temperature range, T_J	-40°C to 150°C
Storage temperature range, T_{stg}	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to LGND and PGND.
 2. Each power DMOS source is internally connected to PGND.
 3. Pulse duration $\leq 100 \mu\text{s}$ and duty cycle $\leq 2\%$.
 4. DRAIN supply voltage = 15 V, starting junction temperature (T_{JS}) = 25°C, $L = 210 \text{ mH}$, $I_{AS} = 600 \text{ mA}$ (see Figure 6).

DISSIPATION RATING TABLE

PACKAGE	$T_C \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_C = 25^\circ\text{C}$	$T_C = 125^\circ\text{C}$ POWER RATING
DW	1750 mW	14 mW/°C	350 mW
NE	2500 mW	20 mW/°C	500 mW

TPIC6A595 POWER LOGIC 8-BIT SHIFT REGISTER

SLIS005B – APRIL 1993 – REVISED MAY 2005

recommended operating conditions

	MIN	MAX	UNIT
Logic supply voltage, V_{CC}	4.5	5.5	V
High-level input voltage, V_{IH}	$0.85 V_{CC}$	V_{CC}	V
Low-level input voltage, V_{IL}	0	$0.15 V_{CC}$	V
Pulsed drain output current, $T_C = 25^\circ\text{C}$, $V_{CC} = 5\text{ V}$ (see Notes 3 and 5)	-1.8	0.6	A
Setup time, SER IN high before SRCK \uparrow , t_{SU} (see Figure 2)	10		ns
Hold time, SER IN high after SRCK \uparrow , t_H (see Figure 2)	10		ns
Pulse duration, t_W (see Figure 2)	20		ns
Operating case temperature, T_C	-40	125	$^\circ\text{C}$

electrical characteristics, $V_{CC} = 5\text{ V}$, $T_C = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSX}$ Drain-to-source breakdown voltage	$I_D = 1\text{ mA}$	50			V
V_{SD} Source-to-drain diode forward voltage	$I_F = 350\text{ mA}$, See Note 3		0.8	1.1	V
V_{OH} High-level output voltage, SER OUT	$I_{OH} = -20\ \mu\text{A}$	$V_{CC} - 0.1$	V_{CC}		V
	$I_{OH} = -4\text{ mA}$	$V_{CC} - 0.5$	$V_{CC} - 0.2$		
V_{OL} Low-level output voltage, SER OUT	$I_{OL} = 20\ \mu\text{A}$		0	0.1	V
	$I_{OL} = 4\text{ mA}$		0.2	0.5	
I_{IH} High-level input current	$V_I = V_{CC}$			1	μA
I_{IL} Low-level input current	$V_I = 0$			-1	μA
$I_{O(chop)}$ Output current at which chopping starts	$T_C = 25^\circ\text{C}$, See Note 5 and Figures 3 and 4	0.6	0.8	1.1	A
I_{CC} Logic supply current	$I_O = 0$, $V_I = V_{CC}$ or 0		0.5	5	mA
$I_{CC(FRQ)}$ Logic supply current at frequency	$f_{SRCK} = 5\text{ MHz}$, $V_I = V_{CC}$ or 0, $I_O = 0$, $V_{CC} = 5\text{ V}$, $C_L = 30\text{ pF}$, See Figure 7		1.3		mA
$I_{(nom)}$ Nominal current	$V_{DS(on)} = 0.5\text{ V}$, $V_{CC} = 5\text{ V}$, $I_{(nom)} = I_D$, $T_C = 85^\circ\text{C}$, See Notes 5, 6, and 7		350		mA
I_D Drain current, off-state	$V_{DS} = 40\text{ V}$, $T_C = 25^\circ\text{C}$		0.1	1	μA
	$V_{DS} = 40\text{ V}$, $T_C = 125^\circ\text{C}$		0.2	5	
$r_{DS(on)}$ Static drain-source on-state resistance	$I_D = 350\text{ mA}$, $T_C = 25^\circ\text{C}$	See Notes 5 and 6 and Figures 10 and 11	1	1.5	Ω
	$I_D = 350\text{ mA}$, $T_C = 125^\circ\text{C}$		1.7	2.5	
	$I_D = 350\text{ mA}$, $T_C = 40^\circ\text{C}$				

- NOTES: 3. Pulse duration $\leq 100\ \mu\text{s}$ and duty cycle $\leq 2\%$.
5. Technique should limit $T_J - T_C$ to 10°C maximum.
6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at $T_C = 85^\circ\text{C}$.

TPIC6A595

POWER LOGIC 8-BIT SHIFT REGISTER

SLIS005B – APRIL 1993 – REVISED MAY 2005

switching characteristics, $V_{CC} = 5\text{ V}$, $T_C = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PHL}	Propagation delay time, high-to-low-level output from \overline{G}	$C_L = 30\text{ pF}$, $I_D = 350\text{ mA}$, See Figures 1, 2, and 12		30		ns
t_{PLH}	Propagation delay time, low-to-high-level output from \overline{G}			125		ns
t_r	Rise time, drain output			60		ns
t_f	Fall time, drain output			30		ns
t_a	Reverse-recovery-current rise time	$I_F = 350\text{ mA}$, $di/dt = 20\text{ A}/\mu\text{s}$, See Notes 5 and 6 and Figure 5		100		ns
t_{rr}	Reverse-recovery time			300		ns

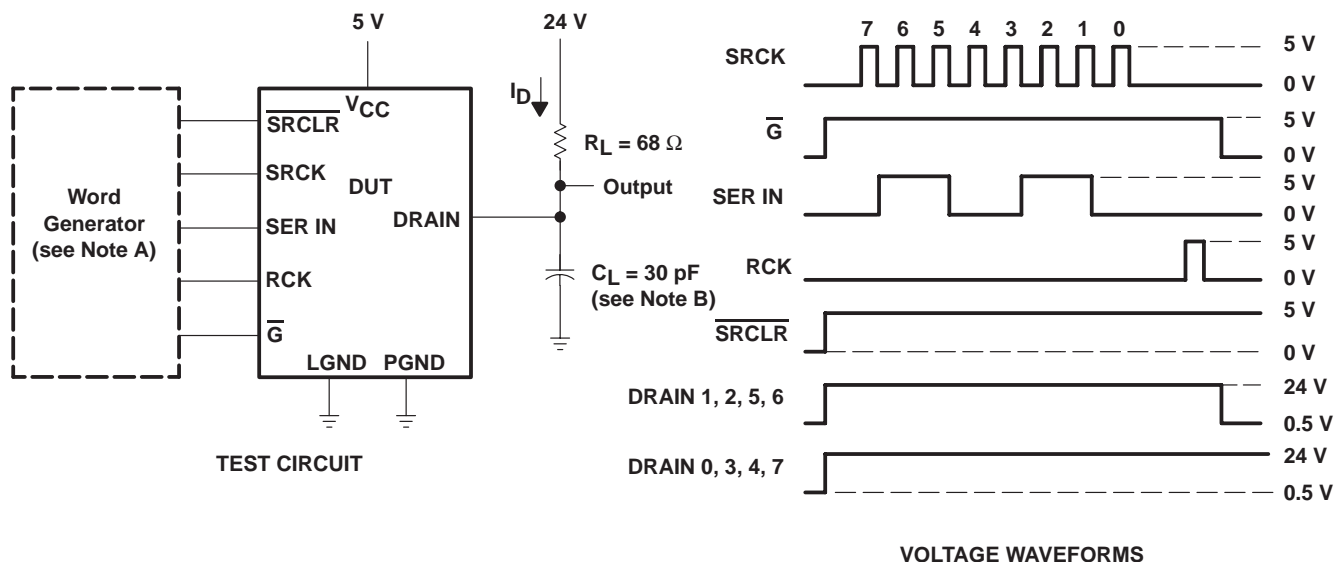
NOTES: 5. Technique should limit $T_J - T_C$ to 10°C maximum.

6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

thermal resistance

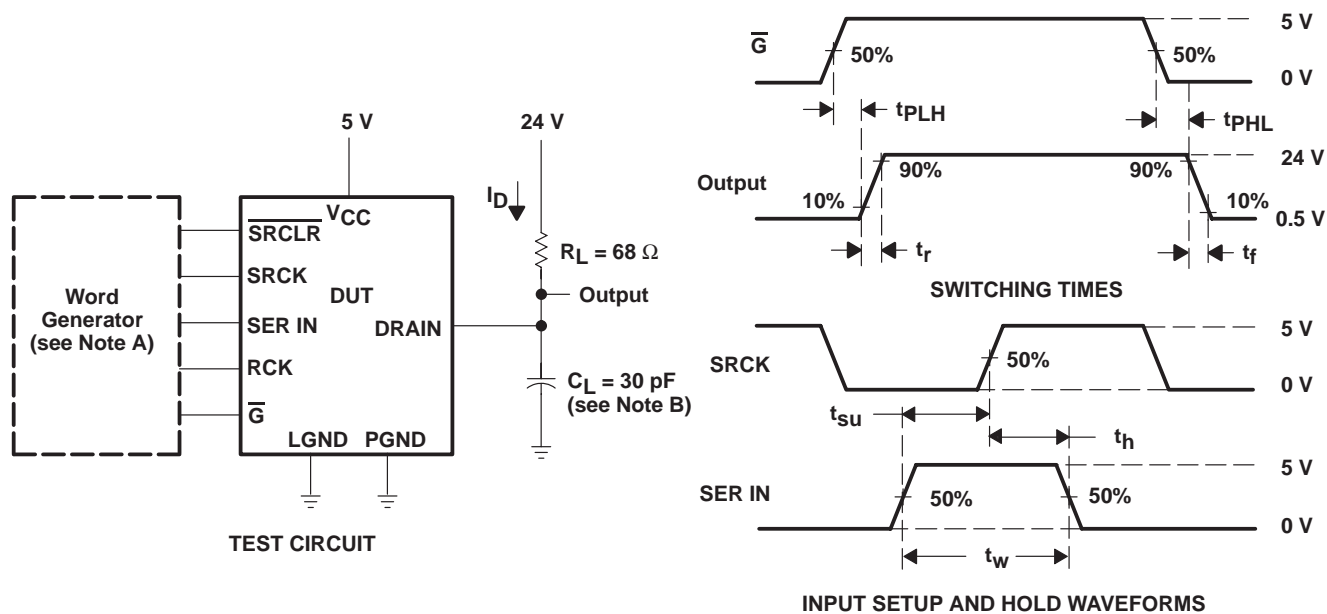
PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
$R_{\theta JC}$	Thermal resistance, junction-to-case	DW		10	$^\circ\text{C}/\text{W}$
		NE	All eight outputs with equal power	10	
$R_{\theta JA}$	Thermal resistance, junction-to-ambient	DW		50	$^\circ\text{C}/\text{W}$
		NE	All eight outputs with equal power	50	

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The word generator has the following characteristics: $t_r \leq 10$ ns, $t_f \leq 10$ ns, $t_w = 300$ ns, pulsed repetition rate (PRR) = 5 kHz, $Z_O = 50 \Omega$.
B. C_L includes probe and jig capacitance.

Figure 1. Resistive Load Operation



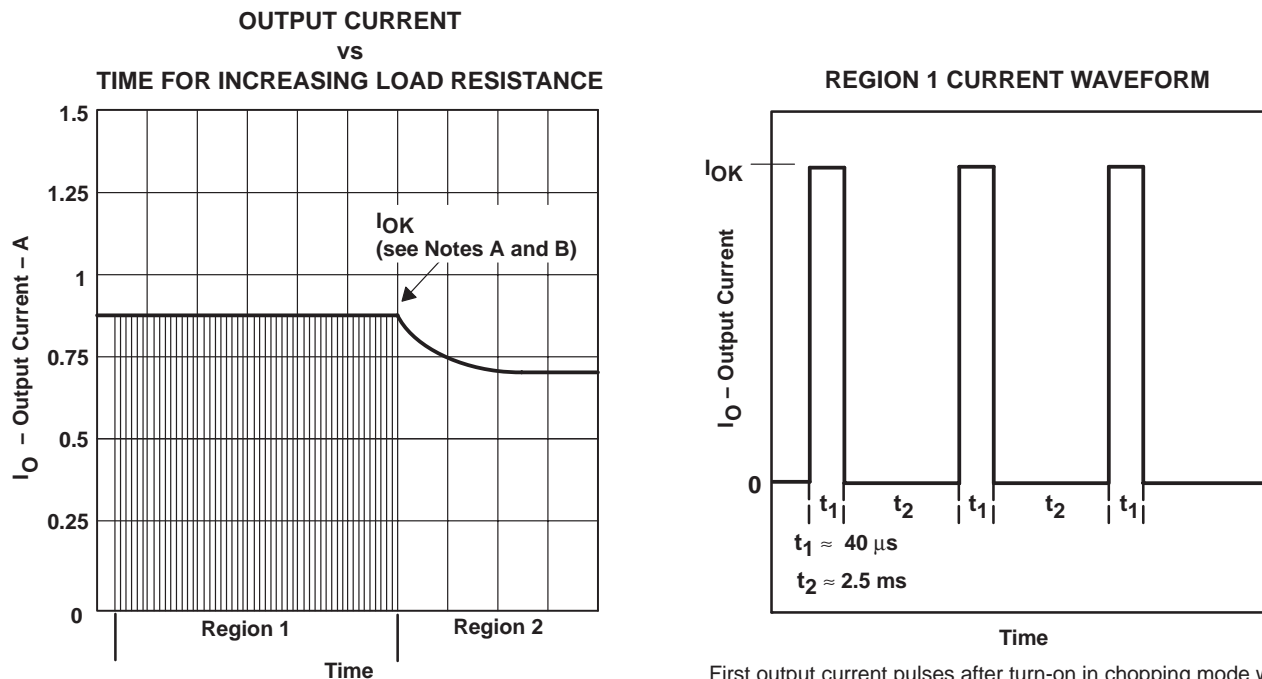
- NOTES: A. The word generator has the following characteristics: $t_r \leq 10$ ns, $t_f \leq 10$ ns, $t_w = 300$ ns, pulsed repetition rate (PRR) = 5 kHz, $Z_O = 50 \Omega$.
B. C_L includes probe and jig capacitance.

Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

TPIC6A595 POWER LOGIC 8-BIT SHIFT REGISTER

SLIS005B – APRIL 1993 – REVISED MAY 2005

PARAMETER MEASUREMENT INFORMATION



First output current pulses after turn-on in chopping mode with resistive load.

- NOTES: A. Figure 3 illustrates the output current characteristics of the device energizing a load having initially low, increasing resistance, e.g., an incandescent lamp. In region 1, chopping occurs and the peak current is limited to I_{OK} . In region 2, output current is continuous. The same characteristics occur in reverse order when the device energizes a load having an initially high, decreasing resistance.
- B. Region 1 duty cycle is approximately 2%.

Figure 3. Chopping-Mode Characteristics

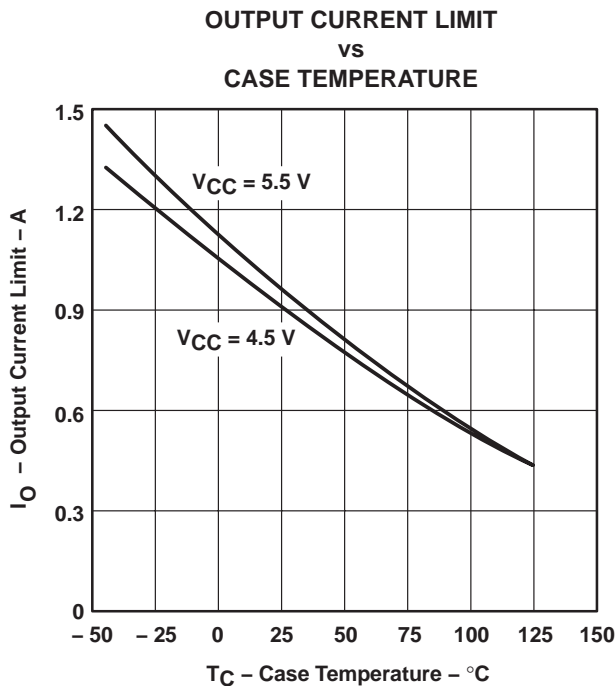
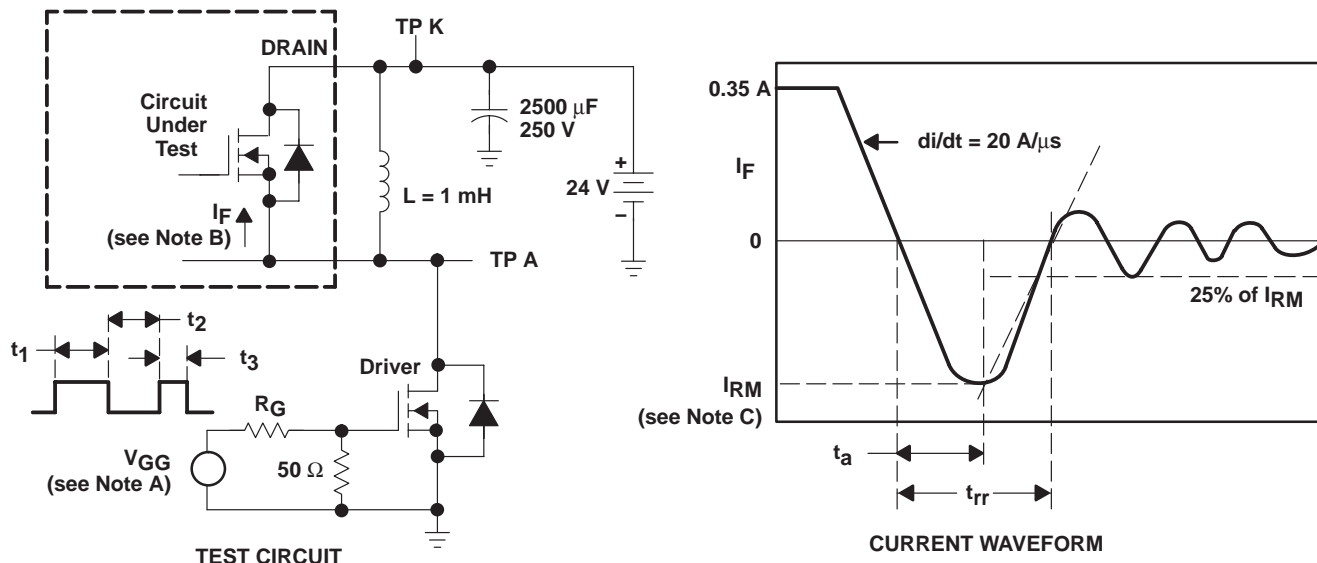


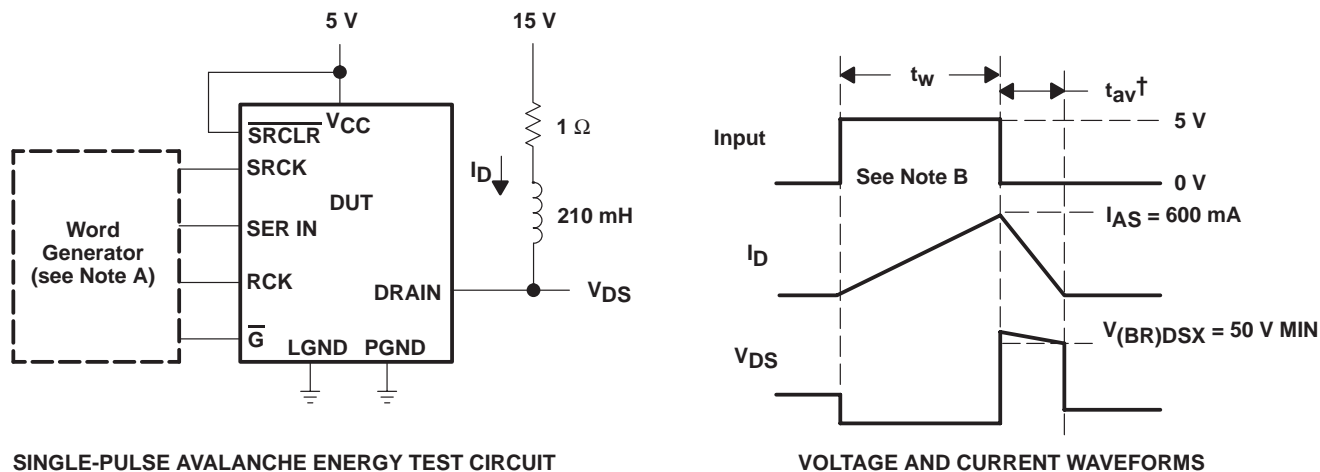
Figure 4

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The V_{GG} amplitude and R_G are adjusted for $di/dt = 20 \text{ A}/\mu\text{s}$. A V_{GG} double-pulse train is used to set $I_F = 0.35 \text{ A}$, where $t_1 = 10 \mu\text{s}$, $t_2 = 7 \mu\text{s}$, and $t_3 = 3 \mu\text{s}$.
 B. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.
 C. I_{RM} = maximum recovery current

Figure 5. Reverse-Recovery-Current Test Circuit and Waveforms of Source-Drain Diode



- † Non JEDEC symbol for avalanche time.
 NOTES: A. The word generator has the following characteristics: $t_r \leq 10 \text{ ns}$, $t_f \leq 10 \text{ ns}$, $Z_0 = 50 \Omega$.
 B. Input pulse duration, t_w , is increased until peak current $I_{AS} = 600 \text{ mA}$.
 Energy test level is defined as $E_{AS} = (I_{AS} \times V_{(BR)DSX} \times t_{av})/2 = 75 \text{ mJ}$.

Figure 6. Single-Pulse Avalanche Energy Test Circuit and Waveforms

TPIC6A595 POWER LOGIC 8-BIT SHIFT REGISTER

SLIS005B – APRIL 1993 – REVISED MAY 2005

TYPICAL CHARACTERISTICS

**SUPPLY CURRENT
vs
FREQUENCY**

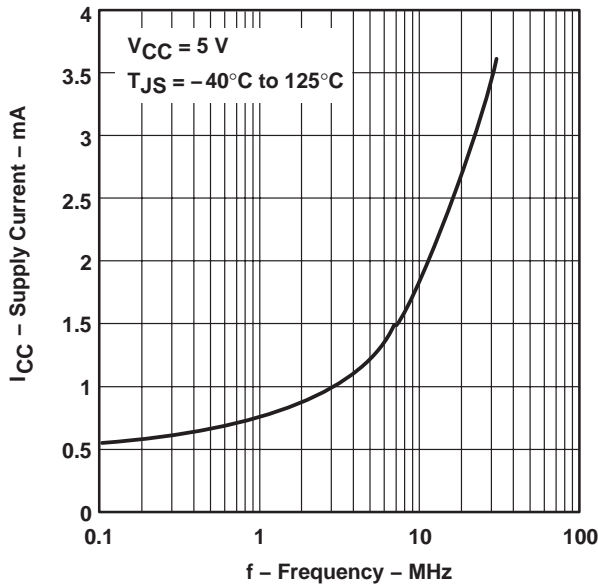


Figure 7

**MAXIMUM CONTINUOUS
DRAIN CURRENT OF EACH OUTPUT
vs
NUMBER OF OUTPUTS CONDUCTING
SIMULTANEOUSLY**

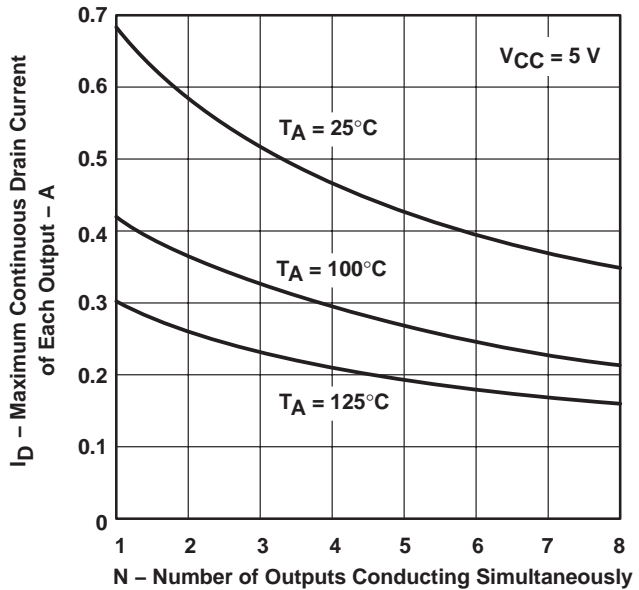


Figure 8

**MAXIMUM PEAK DRAIN CURRENT
OF EACH OUTPUT
vs
NUMBER OF OUTPUTS CONDUCTING
SIMULTANEOUSLY**

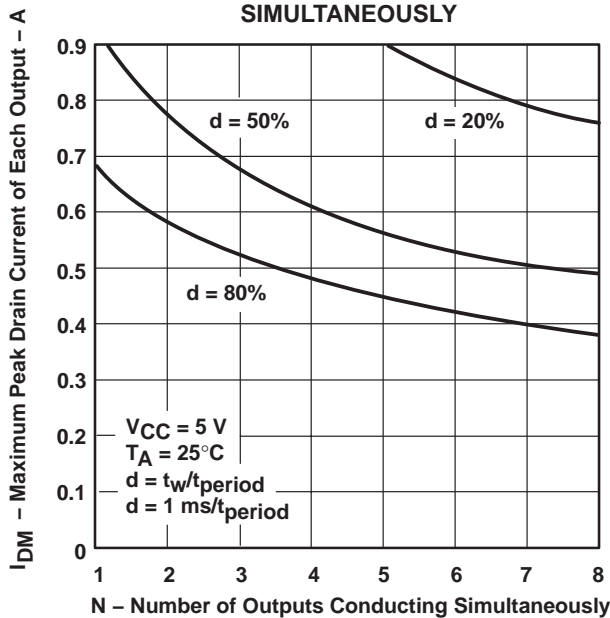


Figure 9

**STATIC DRAIN-SOURCE ON-STATE RESISTANCE
vs
DRAIN CURRENT**

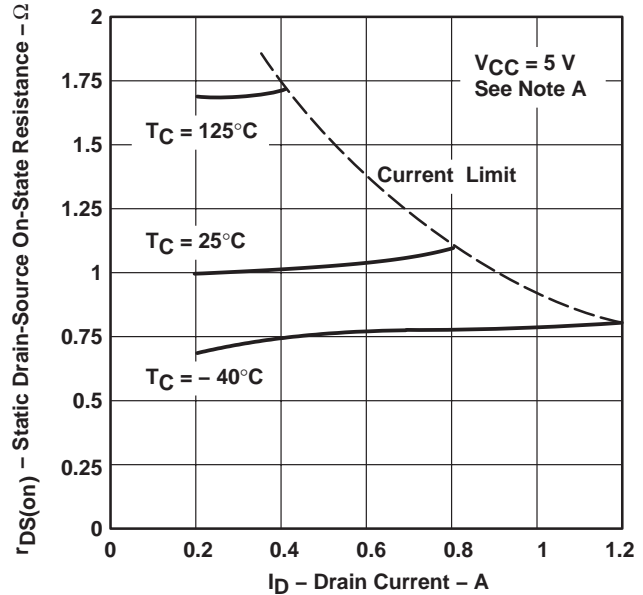


Figure 10

NOTE A: Technique should limit $T_J - T_C$ to 10°C maximum.

TYPICAL CHARACTERISTICS

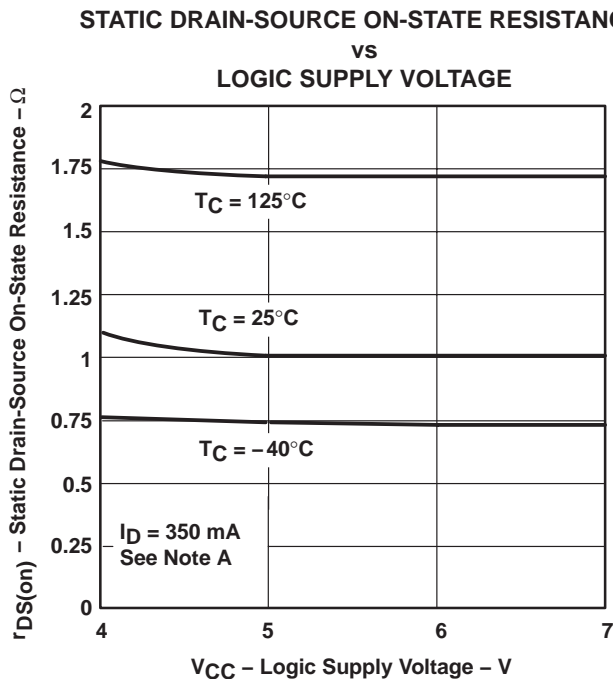


Figure 11

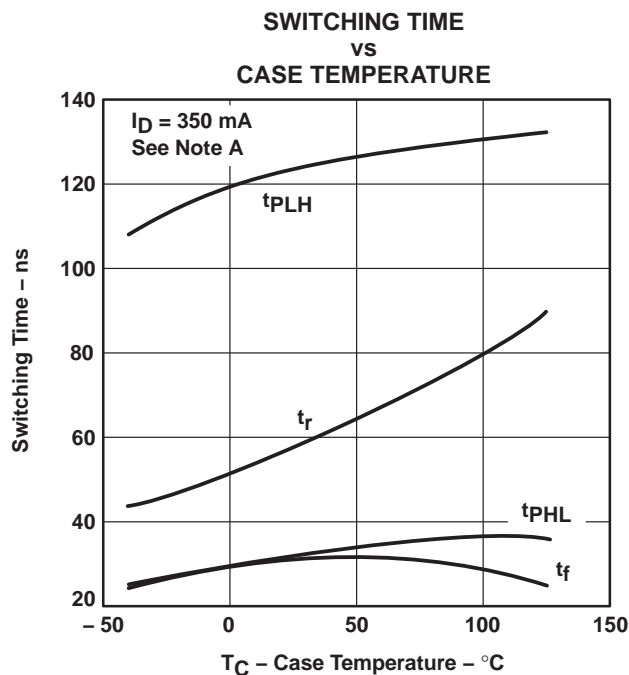


Figure 12

NOTE A: Technique should limit $T_J - T_C$ to 10°C maximum.

THERMAL INFORMATION

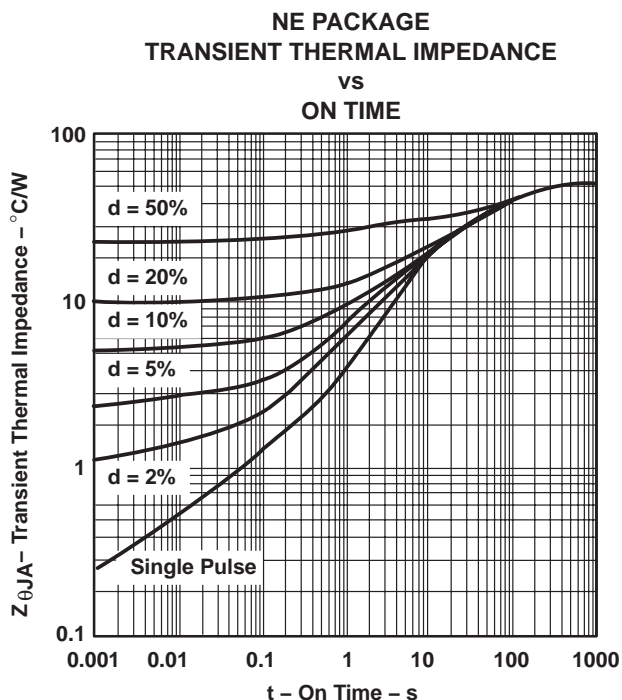


Figure 13

The single-pulse curve represents measured data. The curves for various pulse durations are based on the following equation:

$$Z_{\theta JA} = \left| \frac{t_w}{t_c} \right| R_{\theta JA} + \left| 1 - \frac{t_w}{t_c} \right| Z_{\theta}(t_w + t_c) + Z_{\theta}(t_w) - Z_{\theta}(t_c)$$

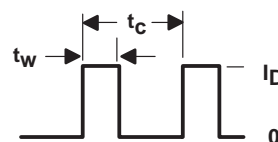
Where:

$Z_{\theta}(t_w)$ = the single-pulse thermal impedance for $t = t_w$ seconds

$Z_{\theta}(t_c)$ = the single-pulse thermal impedance for $t = t_c$ seconds

$Z_{\theta}(t_w + t_c)$ = the single-pulse thermal impedance for $t = t_w + t_c$ seconds

$$d = t_w/t_c$$



TPIC6A595 POWER LOGIC 8-BIT SHIFT REGISTER

SLIS005B – APRIL 1993 – REVISED MAY 2005

Revision History

DATE	REV	PAGE	SECTION	DESCRIPTION
5/18/05	B	7	Figure 1	Changed <u>SRCLR</u> timing diagram and changed title on Drain timing diagrams
1/1/95	A		—	—
4/1/93	*			Original reversion

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.



POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TPIC6A595DW	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6A595DWG4	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6A595DWR	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6A595DWRG4	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6A595NE	ACTIVE	PDIP	NE	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION
REEL DIMENSIONS

TAPE DIMENSIONS


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPIC6A595DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPIC6A595DWR	SOIC	DW	24	2000	367.0	367.0	45.0

DW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
 - D. Falls within JEDEC MS-013 variation AD.

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46C and to discontinue any product or service per JESD48B. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have **not** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components which meet ISO/TS16949 requirements, mainly for automotive use. Components which have not been so designated are neither designed nor intended for automotive use; and TI will not be responsible for any failure of such components to meet such requirements.

Products

Audio	www.ti.com/audio
Amplifiers	amplifier.ti.com
Data Converters	dataconverter.ti.com
DLP® Products	www.dlp.com
DSP	dsp.ti.com
Clocks and Timers	www.ti.com/clocks
Interface	interface.ti.com
Logic	logic.ti.com
Power Mgmt	power.ti.com
Microcontrollers	microcontroller.ti.com
RFID	www.ti-rfid.com
OMAP Mobile Processors	www.ti.com/omap
Wireless Connectivity	www.ti.com/wirelessconnectivity

Applications

Automotive and Transportation	www.ti.com/automotive
Communications and Telecom	www.ti.com/communications
Computers and Peripherals	www.ti.com/computers
Consumer Electronics	www.ti.com/consumer-apps
Energy and Lighting	www.ti.com/energy
Industrial	www.ti.com/industrial
Medical	www.ti.com/medical
Security	www.ti.com/security
Space, Avionics and Defense	www.ti.com/space-avionics-defense
Video and Imaging	www.ti.com/video

TI E2E Community e2e.ti.com